## Claims

*What is claimed is:*

1. A method of etching an organic dielectric layer over a substrate, comprising:

placing the substrate in an etching chamber;

providing an etchant gas comprising NH3 into the etching chamber; and

generating a plasma from the NH3, which etches the organic dielectric layer.

2. The method, as recited in claim 1, wherein the NH3 has a flow rate between 5 sccm to 1500 sccm.

3. The method, as recited in claim 2, further comprising placing a hard mask over the organic dielectric layer.

4. The method, as recited in claim 3, further comprising:

placing a patterned photoresist layer over the hard mask layer; and

simultaneously stripping the photo resist layer during the etching of the organic dielectric layer.

5. The method, as recited in claim 4, further comprising providing CH3F while providing the etchant gas comprising NH3.

6. The method, as recited in claim 5, wherein the CH3F has a flow rate between 1 sccm to 50 sccm.

7. The method, as recited in claim 6, further comprising providing an etch with an etchant gas comprising CF4, prior to the step of providing the etchant gas comprising NH3.

8. The method, as recited in claim 7, wherein the etchant gas comprising CF4, further comprises C4F8.

9. The method, as recited in claim 8, wherein the etchant gas comprising CF4 further comprises O2.

10. The method, as recited in claim 9, wherein the O2 has a flow rate of between 3 sccm and 300 sccm.

11. The method, as recited in claim 10, wherein the organic dielectric layer is made of an organic low-k material.

12. The method, as recited in claim 1, further comprising placing a hard mask over the organic dielectric layer.

13. The method, as recited in claim 12, further comprising:

placing a patterned photoresist layer over the hard mask layer; and

simultaneously stripping the photo resist layer during the etching of the organic dielectric layer.

14. The method, as recited in claim 1, further comprising providing CH3F while providing the etchant gas comprising NH3.

15. The method, as recited in claim 14, further comprising providing an etch with an etchant gas comprising CF4, prior to the step of providing the etchant gas comprising NH3.

16. The method, as recited in claim 1, wherein the organic dielectric layer is made of an organic low-k material.

17. An integrated circuit formed from an etched organic dielectric layer over a substrate, made from the steps comprising:

placing the substrate in an etching chamber;

providing an etchant gas comprising NH3 into the etching chamber; and

generating a plasma from the NH3, which etches the organic dielectric layer.

18. The integrated circuit, as recited in claim 17, wherein the NH3 has a flow rate between 5 sccm to 1500 sccm.

19. The integrate circuit, as recited in claim 18, further comprising:

placing a hard mask over the organic dielectric layer.

placing a patterned photoresist layer over the hard mask layer; and

simultaneously stripping the photo resist layer during the etching of the organic dielectric layer.